

VERSION TO SHOW CHANGES MADE

In the Claims:

Claims 2, 20, 23, and 36 have been amended as follows.

2. (Amended) A method for manufacturing a semiconductor device comprising steps of:

forming a semiconductor film over a substrate; and

irradiating said semiconductor film by scanning with at least two pairs of linear infrared lights in a predetermined direction,

wherein [one] at least two of said linear infrared lights [is] are located over said substrate and the other [one] at least two of said linear infrared lights [is] are located at a backside of said substrate.

20. (Amended) A method for manufacturing semiconductor device comprising the steps of:

forming an amorphous semiconductor film over a substrate; and

crystallizing the semiconductor film by scanning with at least two pairs of upper and lower linear infrared lights in a predetermined direction,

linear infrared light [is] are located at a backside of said substrate, and

wherein said predetermined direction is coincident with a direction of crystal growth in the semiconductor film.

29. (Amended) A method for manufacturing semiconductor device comprising the steps of:

forming an amorphous semiconductor film over a substrate;
and

crystallizing the semiconductor film by scanning the semiconductor film with at least two pairs of upper and lower linear infrared lights in a direction in order to form and move a temperature gradient the semiconductor film,

wherein said at least two upper linear infrared light [is] are located over said semiconductor film and said at least two lower linear infrared light [is] are located at an underside of said semiconductor film, and

wherein said direction is coincident with a direction of crystal growth in the semiconductor film.

36. (Amended) A method for manufacturing a semiconductor device comprising steps of:

crystallizing said semiconductor film by irradiating said semiconductor film with at least two pairs of linear infrared lights while moving said substrate in a perpendicular to the linear infrared lights,

wherein [one] at least two of said linear infrared lights [is] are located over said substrate and the other [one] at least two of said linear infrared lights [is] are located at a backside of said substrate, and

wherein an irradiating direction is coincident with a direction of crystal growth to be proceeded in the semiconductor film.